

## Feature

- Full diffusion process,capsule type ceramic package
- Amplifying gates
- Double sided cooling

## Typical Application

- High power transmission
- DC and AC motor control,Controlled rectifier
- AC DC switch,phase-controlled rectifying
- Active and reactive invresion

$I_{T(AV)}$	200A
$V_{DRM}/V_{RRM}$	100-6500V
$I_{TSM}$	2.5KA
$I^2t$	$32 \cdot 10^3 a^2s$

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	$T_J$ (°C)	VALUE		UNIT
				Min	Max	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Double side cooled, THS=97°C	125		200	A
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Double side cooled, THS=55°C	125		487	A
$V_{DRM}$ $V_{RRM}$	Repetitive peak off-state voltage Repetitive peak reverse voltage	$V_{DRM} \& V_{RRM} t_p=10ms$ $V_{DSM} \& V_{RSM}=V_{DRM} \& V_{RRM}+100V$	125	100	6500	V
$I_{DRM}$ $I_{RRM}$	Repetitive peak current	$V_{DM}=V_{DRM}$ $V_{RM}=V_{RRM}$	125		30	mA
$I_{TSM}$	Surge on-state current	10ms half sine wave	125		2.5	KA
$I^2t$	$I^2t$ for fusing coordination	$V_R=0.6V_{RRM}$			32	$A^2S^*10$
$V_{TO}$	Threshold voltage		125		0.89	V
$r_T$	On-state slop resistance				1.10	mΩ
$V_{TM}$	Peak on-state voltage	$I_{TM}=628A, F=15KN$	25		2.40	V
dv/dt	Critical rate of rise of-state voltage	$V_{DM}=0.67V_{DRM}$	125		300	V/us
di/dt	Critical rate of rise of on-state current	$V_{DM}=67\% V_{DRM}$ TO 1000A, Gate pulse $t_r \leq 0.5us$ $I_{GM}=1.5A$	125		100	A/us
$I_{TM}$	Reverse recovery current	$I_{TM}=628A, t_q=1000us$ $Di/dt=-20A/us.$ $V_i=50V$	125		100	A
$t_{rr}$	Reverse recovery time				12	us
$Q_{rr}$	Recovery charge				600	uC
$I_{GT}$	Gate trigger current	$V_A=12V, I_A=1A$	25	35	250	mA
$V_{GT}$	Gate trigger voltage			0.8	2.0	V
$I_H$	Holding current			20	150	mA
$V_{GD}$	Npn-trigger gate voltage	$V_{DM}=0.67V_{DRM}$	125	0.3		V
$R_{th(j-h)}$	Thermal resistance Junction to heat sink	At180° sine double side cooled Clamping force 5.0kn			0.065	°C/W
$F_M$	Mounting force			5.3	10	KN
$T_{stq}$	Stored temperature			-40	140	°C
$W_t$	Weight					g
Outline						

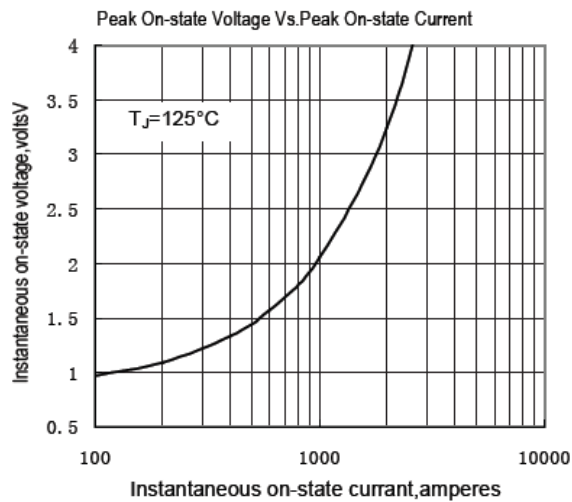


Fig.1

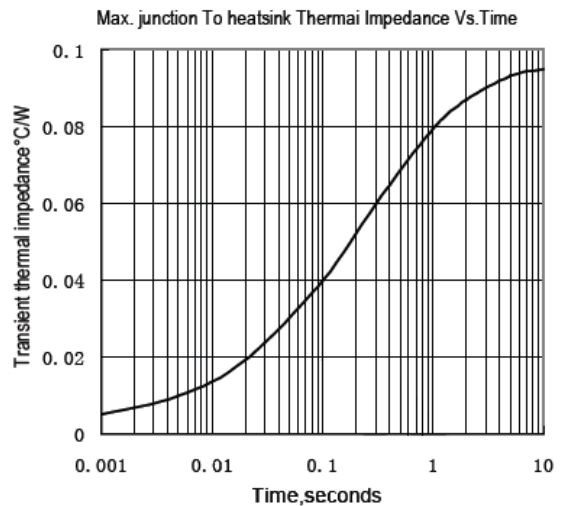


Fig.2

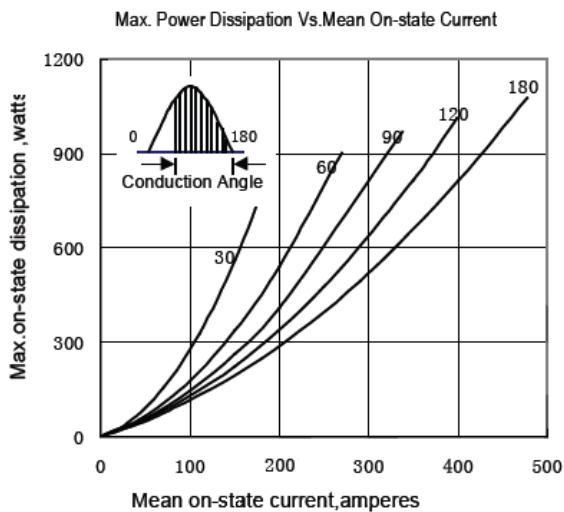


Fig.3

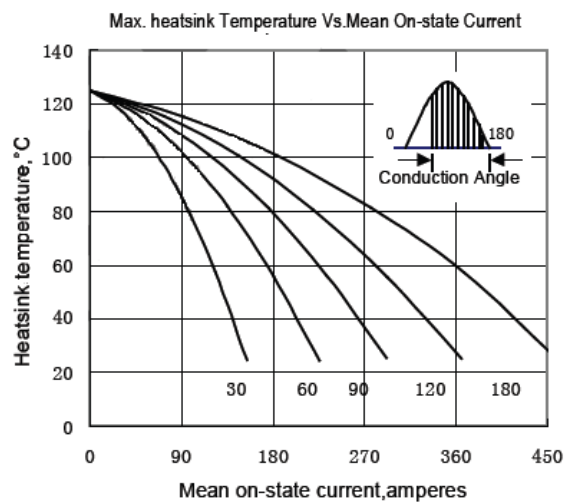


Fig.4

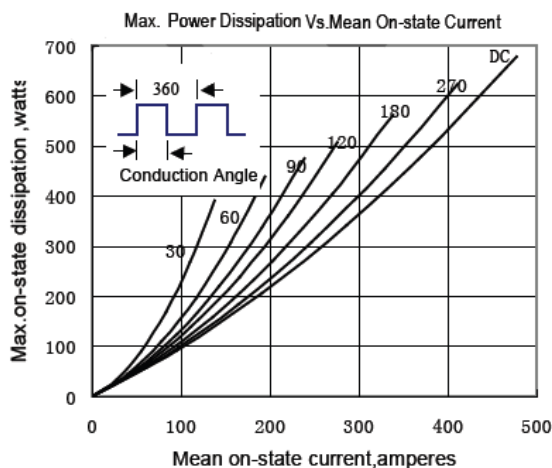


Fig.5

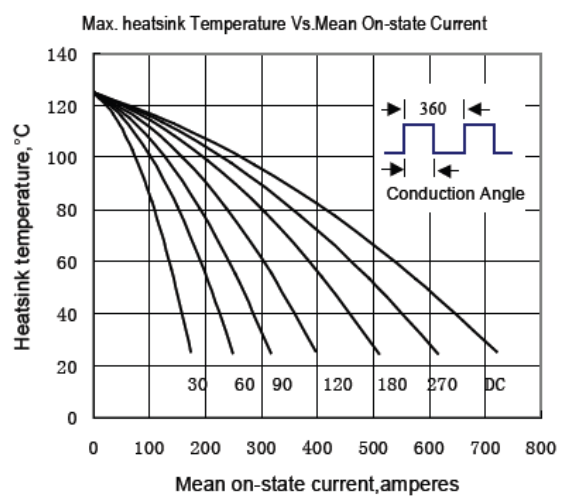


Fig.6

Surge Current Vs.Cycles

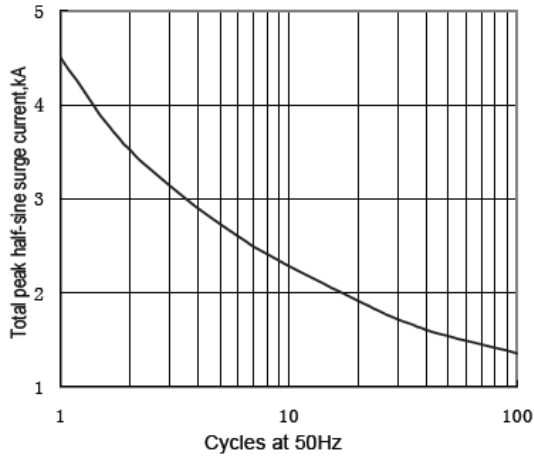


Fig.7

$I^2t$  Vs.Time

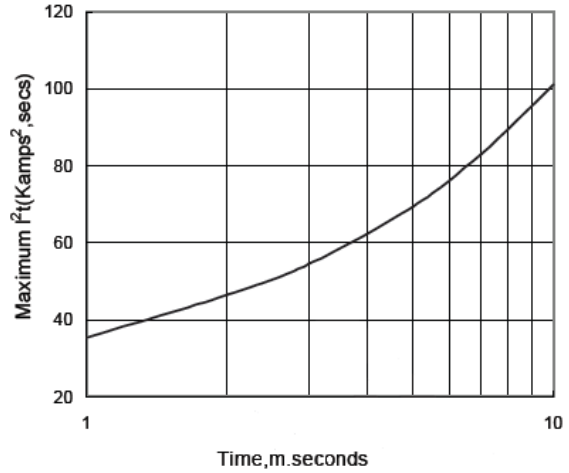


Fig.8

Gate characteristic at 25°C junction temperature

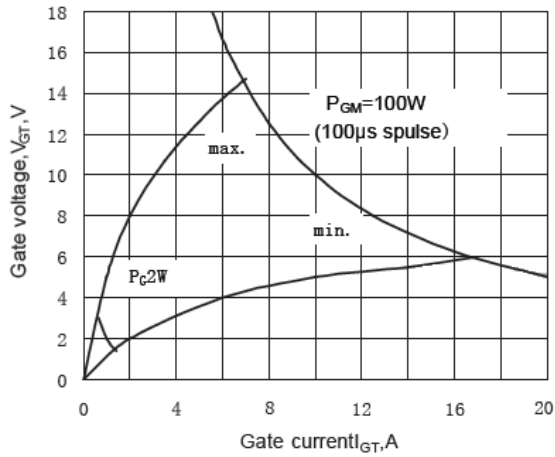


Fig.9

Gate Trigger Zone at varies temperature

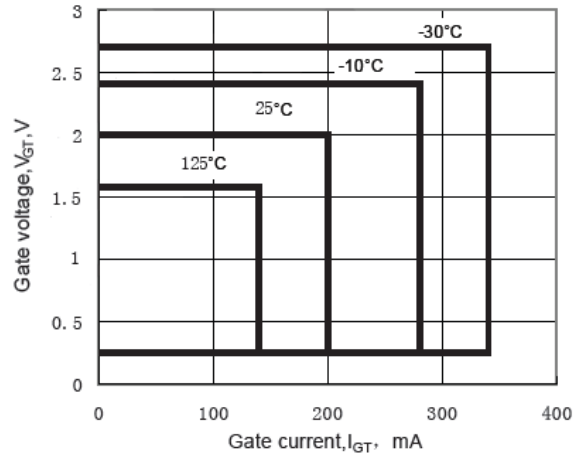


Fig.10

**Outline:**

